Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 07977-004002	Application No. New Continuation Application
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Naoto Kusumoto et al.	
		Filing Date June 25, 2003	Group Art Unit

U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
DM	AA	3,585,088	06/1971	Scwuttke et al.			
	AB	4,195,913	4/1/80	Dourte et al.			
	AC	4,475,027	10/2/84	Pressley			
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Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation Yes	Translation No
DM	AU	ZA8306334	03/1984	China				
	AV	64-76715	03/1989	Japan				
	AW	1-76715	03/1989	Japan				
DM	AX	3-286518	12/1991	Japan				

Examiner Signature	Date Considered
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EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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DM	AY	4-307727	10/1992	Japan	—	—		—

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	ABB	Carluccio et al., "Microstructure of Polycrystalline Silicon Films Obtained by Combined Furnace and Laser Annealing", Appl. Phys. Lett., Vol. 66, No. 11, pp. 1394-1396
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